

Features

- Low $V_{CE(sat)}$
- Fast Switching
- High Ruggedness
- Short-Circuit Rated

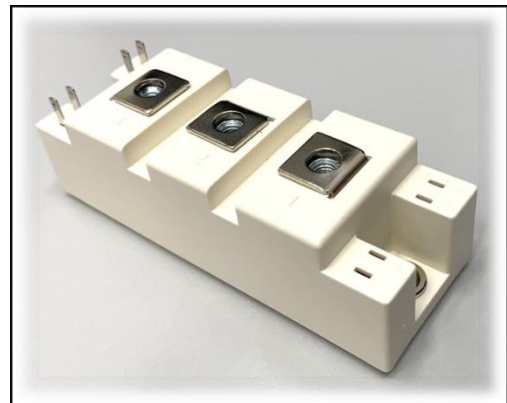


Product Summary

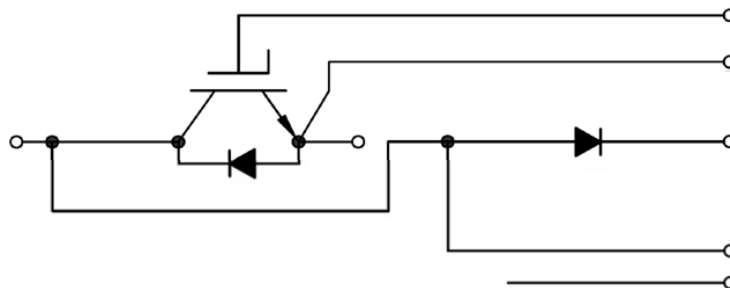
V_{CES}	1200V
I_C	150A
$V_{CE(sat),typ}$	1.6V

Applications

- High Frequency Switching Application
- Industrial Motor Drives
- Medical Applications
- UPS Systems
- Servos



Internal Connection



• IGBT, Brake-Chopper

Absolute Maximum Ratings

Parameter	Symbol	Limit	Unit
Collector-to-Emitter Voltage	V_{CES}	1200	V
Gate-to-Emitter Voltage	V_{GES}	± 20	
Transient Gate-emitter Voltage ($t_p \leq 10\mu s$, $D < 0.010$)		± 30	
Continuous DC Collector Current ($T_c = 100^\circ C$, $T_J = 175^\circ C$)	I_{CDC}	150	A
Repetitive Peak Collector Current ($t_p = 1ms$)	I_{CRM}	300	
Maximum Power Dissipation ($T_c = 25^\circ C$, $T_J = 175^\circ C$)	$P_{D(max)}$	735	W

Electrical Characteristics ^{(1), (2)}

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector-to-Emitter Breakdown Voltage	BV_{CES}	$V_{GE} = 0V, I_C = 250\mu A$	1200	-	-	V
Collector-to-Emitter Leakage Current	I_{CES}	$V_{CE} = 1200V, V_{GE} = 0V$	-	-	5	mA
Gate-to-Emitter Leakage Current	I_{GES}	$V_{CE} = 0V, V_{GE} = \pm 20V$	-	-	400	nA
Gate Threshold Voltage	$V_{GE(th)}$	$V_{CE} = V_{GE}, I_C = 1.5mA$	4.8	6.0	7.2	V
Collector-to-Emitter Saturation Voltage	$V_{CE(sat)}$	$V_{GE} = 15V, I_C = 150A$	-	1.6	2.0	
		$V_{GE} = 15V, I_C = 150A, T_J = 150^\circ C$	-	1.95	-	
		$V_{GE} = 15V, I_C = 150A, T_J = 175^\circ C$	-	2.05	-	
Total Gate Charge	Q_g	$V_{CC} = 600V, V_{GE} = \pm 15V, I_C = 150A$	-	1.44	-	μC
Internal Gate Resistance	R_{Gint}	-	-	3	-	Ω
Input Capacitance	C_{iss}	$V_{CE} = 25V, V_{GE} = 0V, f = 1MHz$	-	9.73	-	nF
Output Capacitance	C_{oss}		-	0.68	-	
Reverse Transfer Capacitance	C_{rss}		-	0.13	-	
Turn-on Delay time	$t_{d(ON)}$	$V_{CC} = 600V, V_{GE} = \pm 15V, R_G = 5.1\Omega, I_C = 150A, L_{load} = 0.82mH, \text{Energy losses include "tail" and diode reverse recovery.}$	-	358	-	ns
Rise Time	t_r		-	48	-	
Turn-off Delay time	$t_{d(OFF)}$		-	452	-	
Fall Time	t_f		-	154	-	
Turn-On Switching Loss	E_{on}		-	8.5	-	mJ
Turn-Off Switching Loss	E_{off}		-	10.0	-	
IGBT Total Switching Loss	E_{ts}		-	18.5	-	
Turn-on Delay time	$t_{d(ON)}$	$V_{CC} = 600V, V_{GE} = \pm 15V, R_G = 5.1\Omega, I_C = 150A, L_{load} = 0.82mH, \text{Energy losses include "tail" and diode reverse recovery. } T_J = 150^\circ C$	-	632	-	ns
Rise Time	t_r		-	60	-	
Turn-off Delay time	$t_{d(OFF)}$		-	470	-	
Fall Time	t_f		-	278	-	
Turn-On Switching Loss	E_{on}		-	14.2	-	mJ
Turn-Off Switching Loss	E_{off}		-	16.8	-	
IGBT Total Switching Loss	E_{ts}		-	31	-	
Short Circuit Collector Current	$I_{C(SC)}$	$V_{GE} = 15V, V_{CC} \leq 600V, t_{SC} \leq 10\mu s$	-	600	-	A

• Diode, Chopper

Absolute Maximum Ratings

Parameter	Symbol	Limit	Unit
Repetitive Peak Reverse Voltage	V_{RRM}	1200	V
Continuous DC Forward Current	I_F	150	A
Repetitive Peak Forward Current ($t_P = 1ms$)	I_{FRM}	300	

Electrical Characteristics ⁽¹⁾

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Diode Forward Voltage	V_F	$I_F = 150A$	-	2.0	2.4	V
		$I_F = 150A$ $T_J = 150^\circ C$	-	1.8	-	
		$I_F = 150A$ $T_J = 175^\circ C$	-	1.75	-	
Diode Reverse-Recovery Charge	Q_{rr}	$V_R = 600V, I_F = 150A,$ $dI_F/dt = -1690 A/\mu s$	-	10.66	-	μC
Diode Peak Reverse-Recovery Current	I_{rrm}		-	99	-	A
Diode Reverse-Recovery Loss	E_{rr}		-	3.35	-	mJ

• Diode, Reverse

Absolute Maximum Ratings

Parameter	Symbol	Limit	Unit
Repetitive Peak Reverse Voltage	V_{RRM}	1200	V
Continuous DC Forward Current	I_F	50	A
Repetitive Peak Forward Current ($t_P=1ms$)	I_{FRM}	100	

Electrical Characteristics ⁽¹⁾

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Diode Forward Voltage	V_F	$I_F = 50A$	-	2.0	2.45	V
		$I_F = 50A$ $T_J = 150^\circ C$	-	1.7	-	
		$I_F = 50A$ $T_J = 175^\circ C$	-	1.65	-	
Diode Reverse-Recovery Charge	Q_{rr}	$V_R = 600V, I_F = 50A,$ $dI_F/dt = -890 A/\mu s$	-	3.37	-	μC
Diode Peak Reverse-Recovery Current	I_{rrm}		-	27	-	A
Diode Reverse-Recovery Loss	E_{rr}		-	1.5	-	mJ

• Module

Absolute Maximum Ratings

Parameter	Symbol	Limit	Unit
Maximum Junction Temperature	T_j	-40 to +175	°C
Operating Junction Temperature	$T_{vj\ op}$	-40 to +150	
Storage Temperature	T_{stg}	-40 to +125	
Isolation Voltage (f = 50Hz, t = 1min)	V_{iso}	2.5	kV

Characteristics

Parameter	Symbol	Min	Typ	Max	Unit
Material of Module Baseplate	-	-	Cu	-	-
Internal Isolation	-	-	Al ₂ O ₃	-	-
Creepage Distance, Terminal to Heatsink	-	-	17	-	mm
Creepage Distance, Terminal to Terminal	-	-	20	-	mm
Clearance, Terminal to Heatsink	-	-	17	-	mm
Clearance, Terminal to Terminal	-	-	9.5	-	mm
Stray Inductance, Module	L_{SCE}	-	30	-	nH
Module Lead Resistance, Terminal to Chip	$R_{CC'+EE'}$	-	0.65	-	mΩ
Junction-to-Case Thermal Resistance, per IGBT, Brake-Chopper	$R_{\theta JC}$	-	0.17	-	°C/W
Junction-to-Case Thermal Resistance, per Diode, Chopper		-	0.26	-	
Junction-to-Case Thermal Resistance, per Diode, Reverse		-	0.68	-	
Case-to-Heatsink Thermal Resistance, per IGBT, Brake-Chopper	$R_{\theta CH}$	-	0.08	-	°C/W
Case-to-Heatsink Thermal Resistance, per Diode, Chopper		-	0.15	-	
Case-to-Heatsink Thermal Resistance, per Diode, Reverse		-	0.41	-	
Case-to-Heatsink Thermal Resistance, per Module		-	0.05	-	
Mounting Torque for Module Mounting, Screw M6	M	3.0	-	5.0	Nm
Terminal Connection Torque, Screw M5	M	2.5	-	5.0	Nm
Weight per Module	G	-	160	-	g

(1) $T_j = 25^\circ\text{C}$ unless otherwise specified

(2) t_r : from 10% of I_c to 90% of I_c ; t_f : from 90% of I_c to 10% of I_c ;

E_{on} : from 10% of V_{GE} to 10% of V_{CE} ; E_{off} : from 90% of V_{GE} to 10% of I_c .

• **Typical Electrical Characteristics**

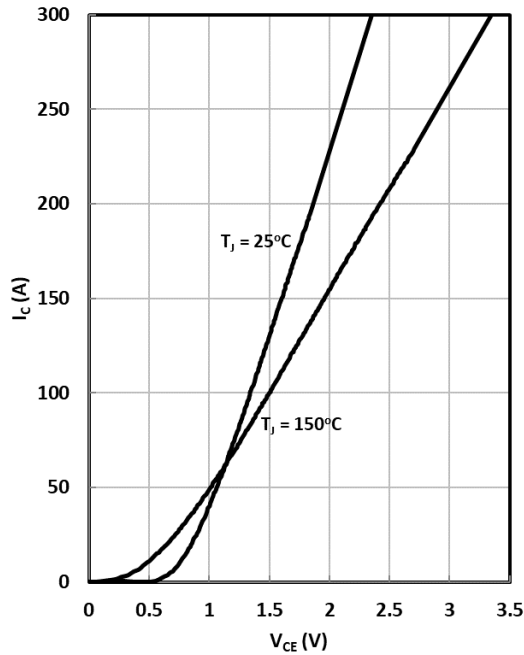


Fig. 1 IGBT (Brake-Chopper) Output Characteristics

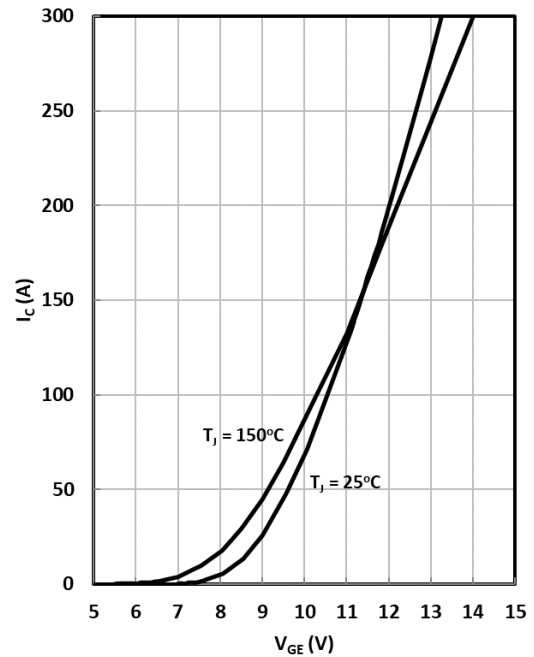


Fig. 2 IGBT (Brake-Chopper) Transfer Characteristics

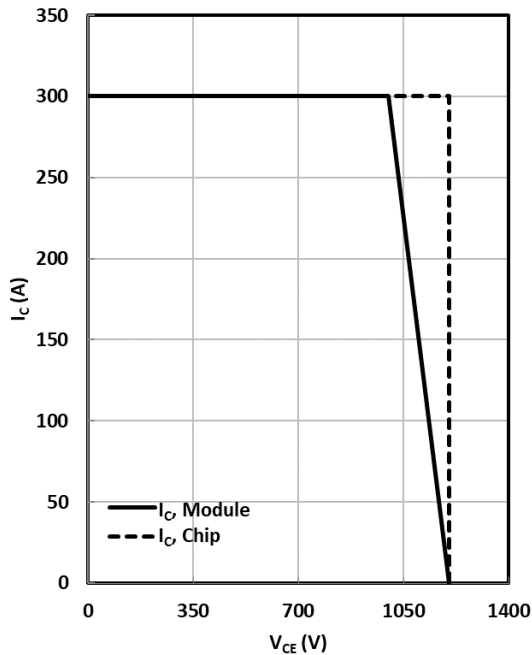


Fig. 3 RBSOA

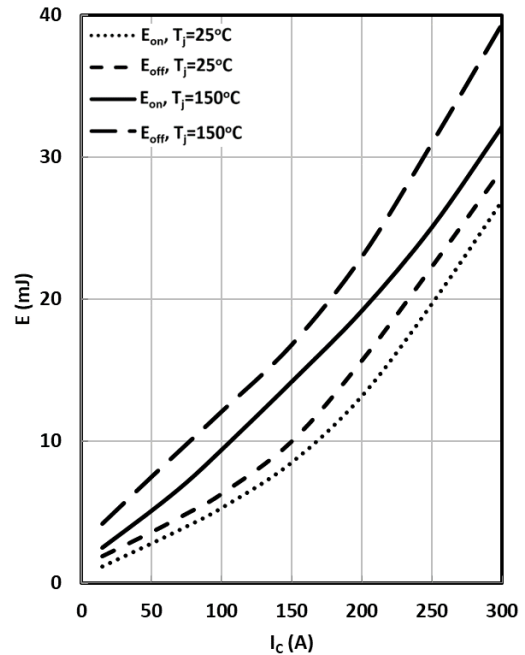


Fig. 4 IGBT (Brake-Chopper) Switching Loss vs. I_C
($V_{CC} = 600\text{V}$, $V_{GE} = \pm 15\text{V}$, $R_G = 5.1\Omega$)

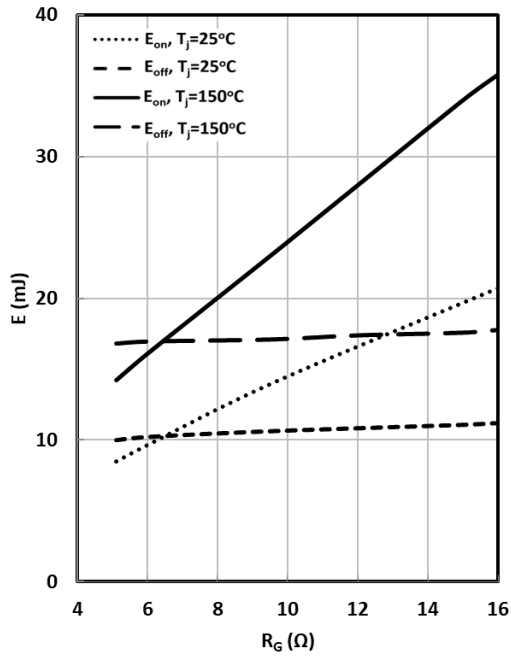


Fig. 5 IGBT (Brake-Chopper) Switching Loss vs. R_G
($V_{CC} = 600V$, $V_{GE} = \pm 15V$, $I_C = 150A$)

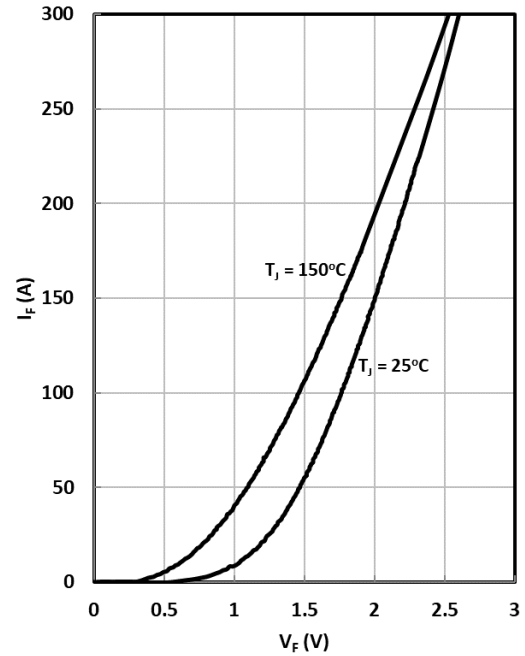


Fig. 6 Diode (Chopper) output characteristics

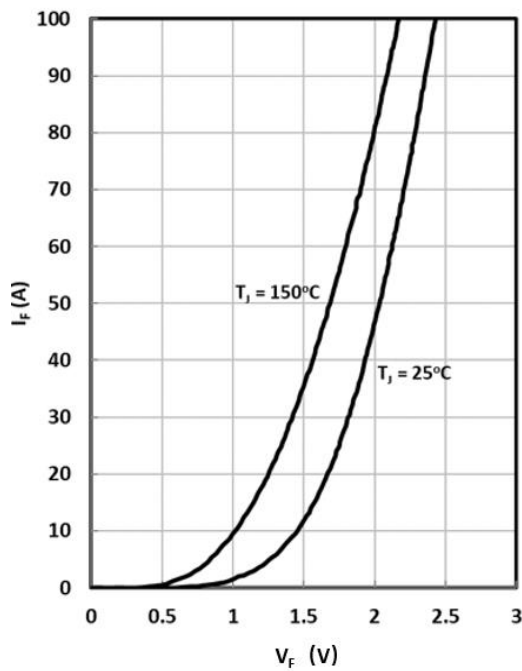
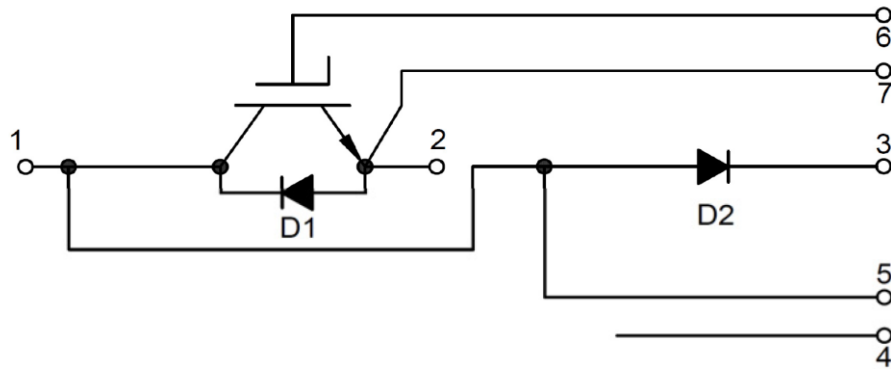
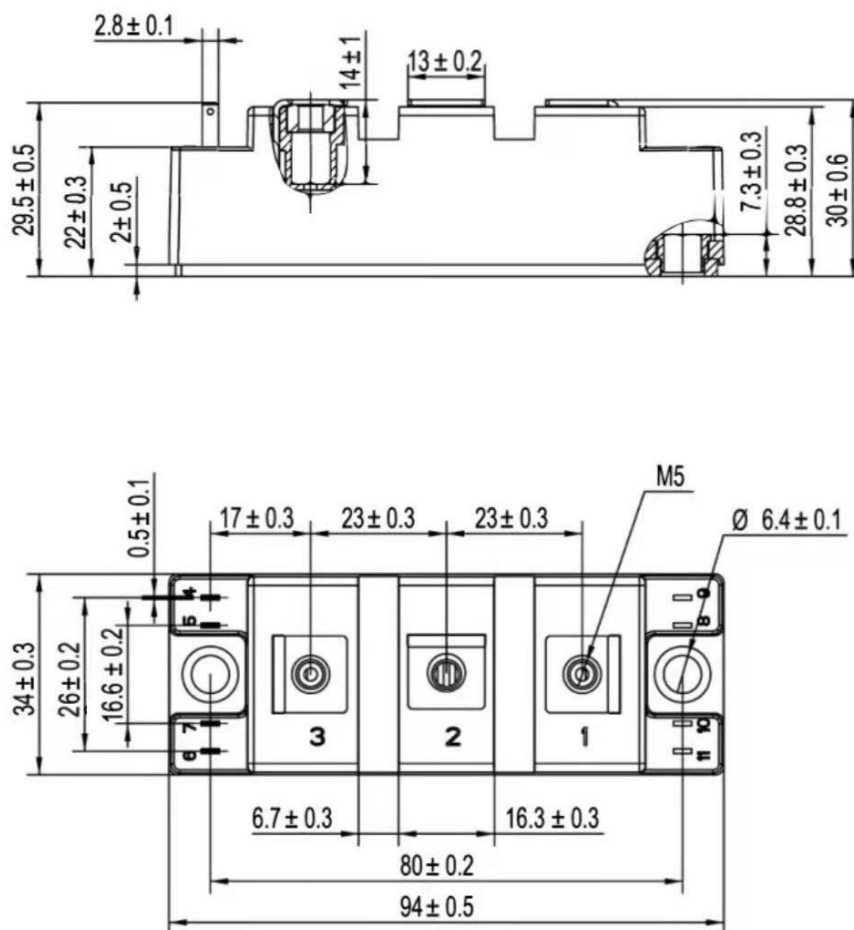


Fig. 7 Diode (Reverse) output characteristics

- Circuit diagram



- Package Dimensions



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